NPN HIGH CURRENT SWITCHING

TABLE 12 — NPN SILICON PLANAR HIGH CURRENT SWITCHING TRANSISTORS

The transistors shown in this table are designed for high current, high dissipation switching applications in Industrial and Military equipments.

The table should be referred to in conjunction with the LF Power Transistor Section which contains full details of the available range of High Power Transistors.

The devices are listed in order of decreasing Breakdown Voltages (V_{CB} and V_{CEO}), decreasing Collector Current (I_C), Power Dissipation (P_{tot}), etc.

Type	V_{CB} V	V_{CEO} V	Max I_C A	Max $V_{CE(sat)}$† at V	I_C A	I_B A	h_{FE} Min.	h_{FE} Max.	h_{FE} at I_C A	Switching times (Typ.) at t_{on} ns	t_{off} ns	I_C A	P_{tot} at T_{amb} = 25°C W	Package	Complement
BUY82	150	60	10	1	10	1	40	—	1.5	320	245	10	30	TO-39	BUY92
BUY81	150	60	7.5	1	7.5	0.75	40	—	1	160	430	5	24	TO-39	BUY91
BUY80	150	60	5	1	5	0.5	40	—	0.5	170	200	5	20	TO-39	BUY90
2N3419A	125	80	5*	1	5	0.5	20	60	1	300	1200	1	30	TO-39	—
2N3421A	125	80	5*	1	5	0.5	40	120	1	300	1200	1	30	TO-39	—
BUX34	120	60	5	1	5	0.5	40	150	2	140	180	5	20	TO-39	—
BFX34	120	60	5*	1	5	0.5	40	150	2	140	180	5	5	TO-39	—
BSV64	100	60	5*	1	5	0.5	40	—	2	140	180	5	5	TO-39	—
2N3418A	85	60	5*	1	5	0.5	20	60	1	300	3000	1	30	TO-39	—
2N3420A	85	60	5*	1	5	0.5	40	120	1	300	3000	1	30	TO-39	—

*I_{CM} †Pulsed 300μs

PNP HIGH CURRENT SWITCHING

TABLE 13 — PNP SILICON PLANAR HIGH CURRENT SWITCHING TRANSISTORS

The transistors shown in this table are designed for high current, high dissipation switching applications in Industrial and Military equipments.

This table should be referred to in conjunction with the LF Power Transistor Section which contains full details of the available range of Darlington Transistors.

The devices are listed in order of decreasing Breakdown Voltages (V_{CB} and V_{CEO}), decreasing Collector Current (I_C), Power Dissipation (P_{tot}), etc.

Type	V_{CB} V	V_{CEO} V	Max I_C A	Max $V_{CE(sat)}$† at V	I_C A	I_B A	h_{FE} Min.	h_{FE} Max.	h_{FE} at I_C A	Switching times (Typ.) at t_{on} ns	t_{off} ns	I_C A	P_{tot} at T_{amb} = 25°C W	Package	Complement
BUY92	100	60	7.5	1	7.5	0.75	40	—	1	—	—	—	30	TO-39	BUY82
BUY91	100	60	5	1	5	0.5	40	—	1	—	—	—	24	TO-39	BUY81
BUY90	100	60	3	1	3	0.3	40	—	1	—	—	—	20	TO-39	BUY80

†Pulsed 300μs.